

200354987.

App No.: 10/812,412

Docket No.: 543822005300

Inventor: Steven WANG et al.

Title: METHOD FOR PRODUCING A DEEP TRENCH
CAPACITOR IN A SEMICONDUCTOR SUBSTRATE

1/13

Sheet 1 of 13



FIG 1A

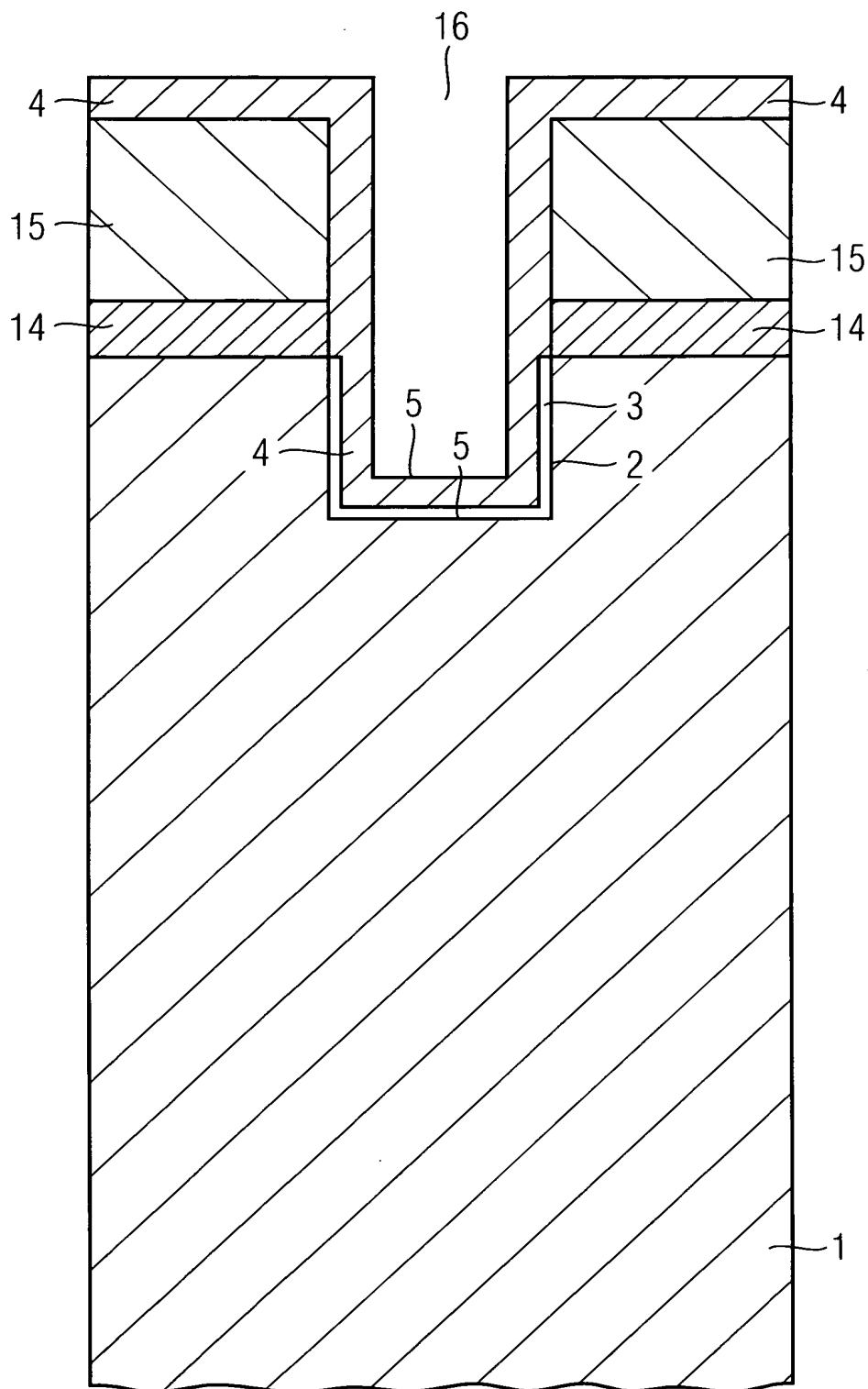


FIG 1B

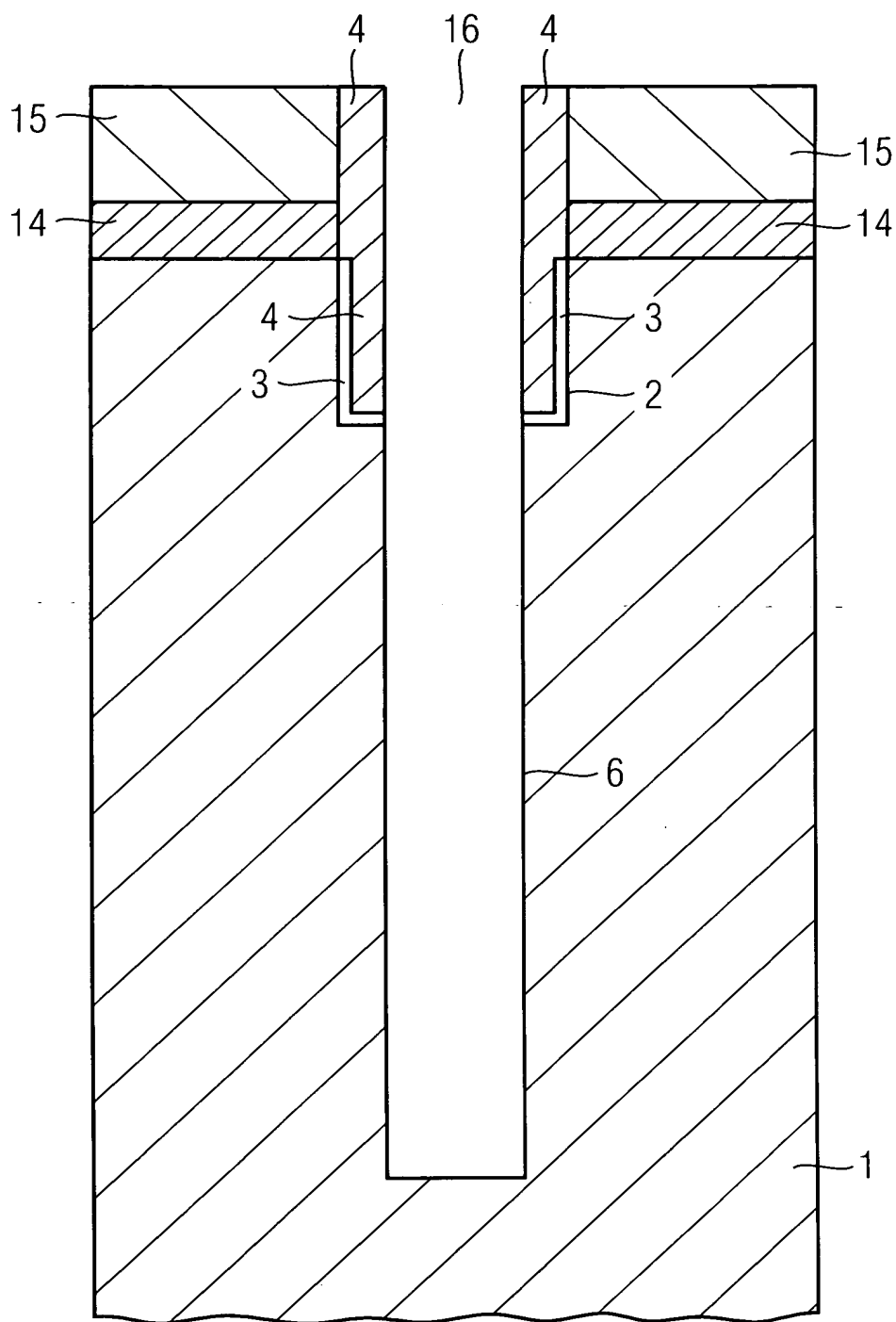


FIG 1C

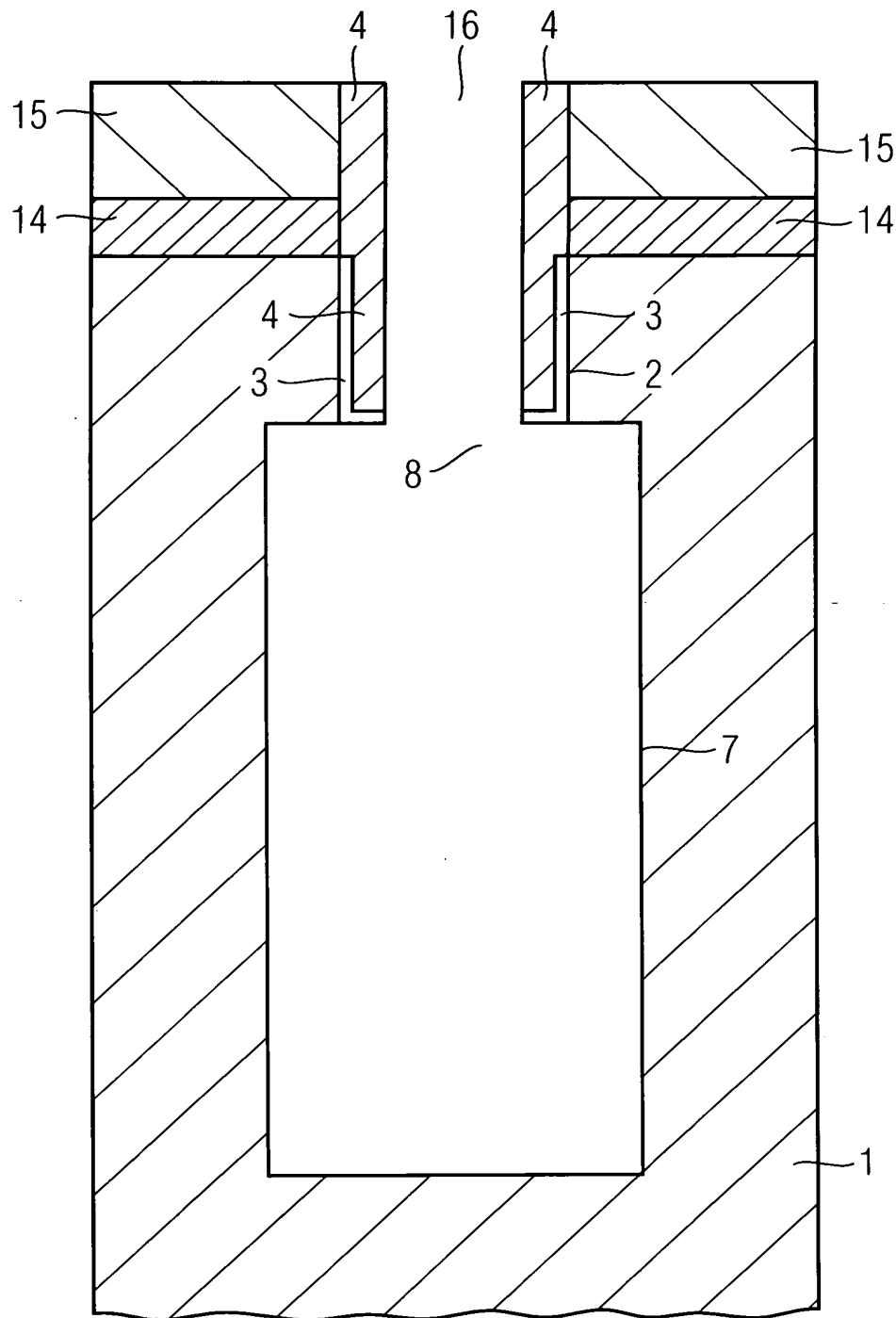


FIG 1D

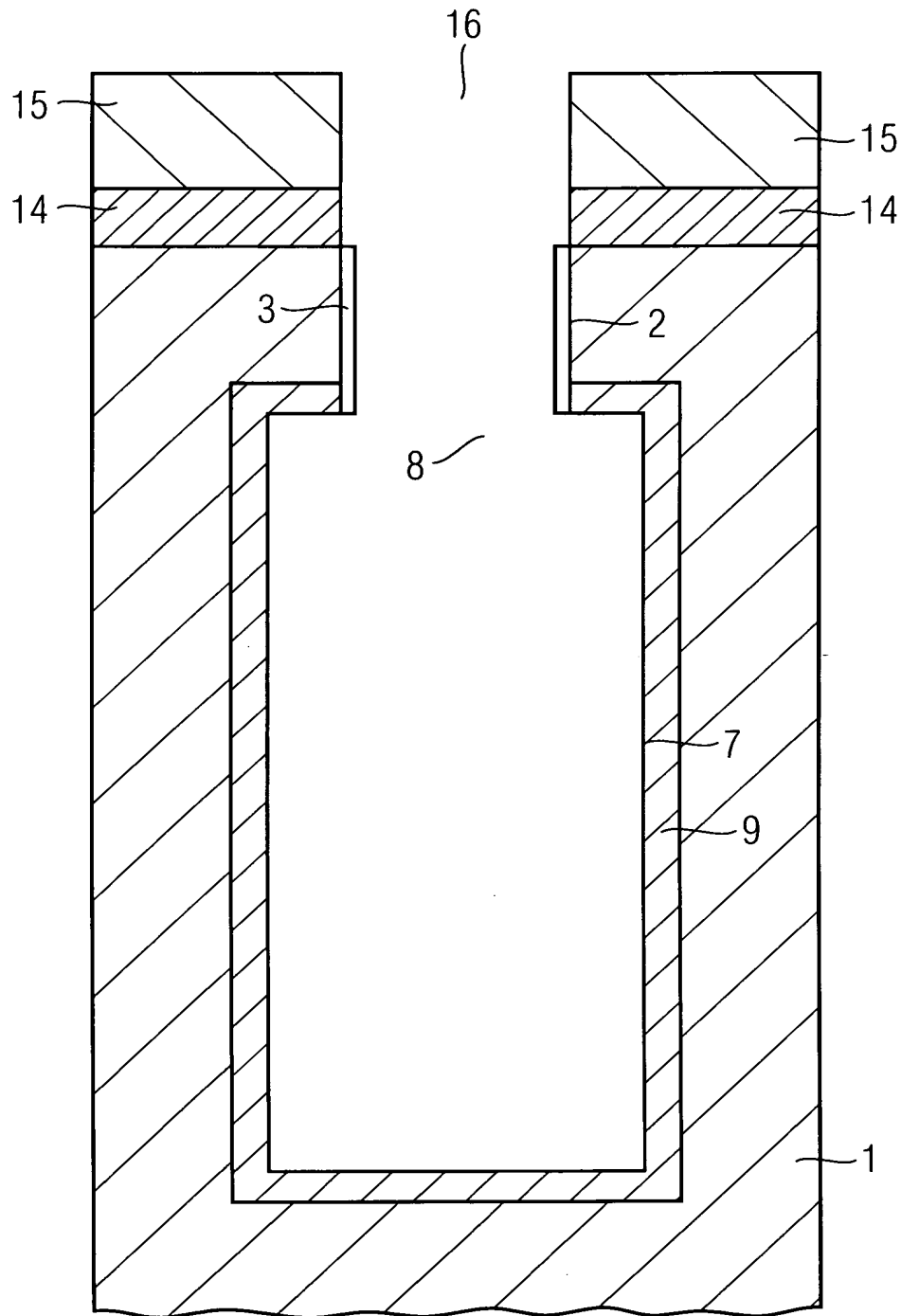


FIG 1E

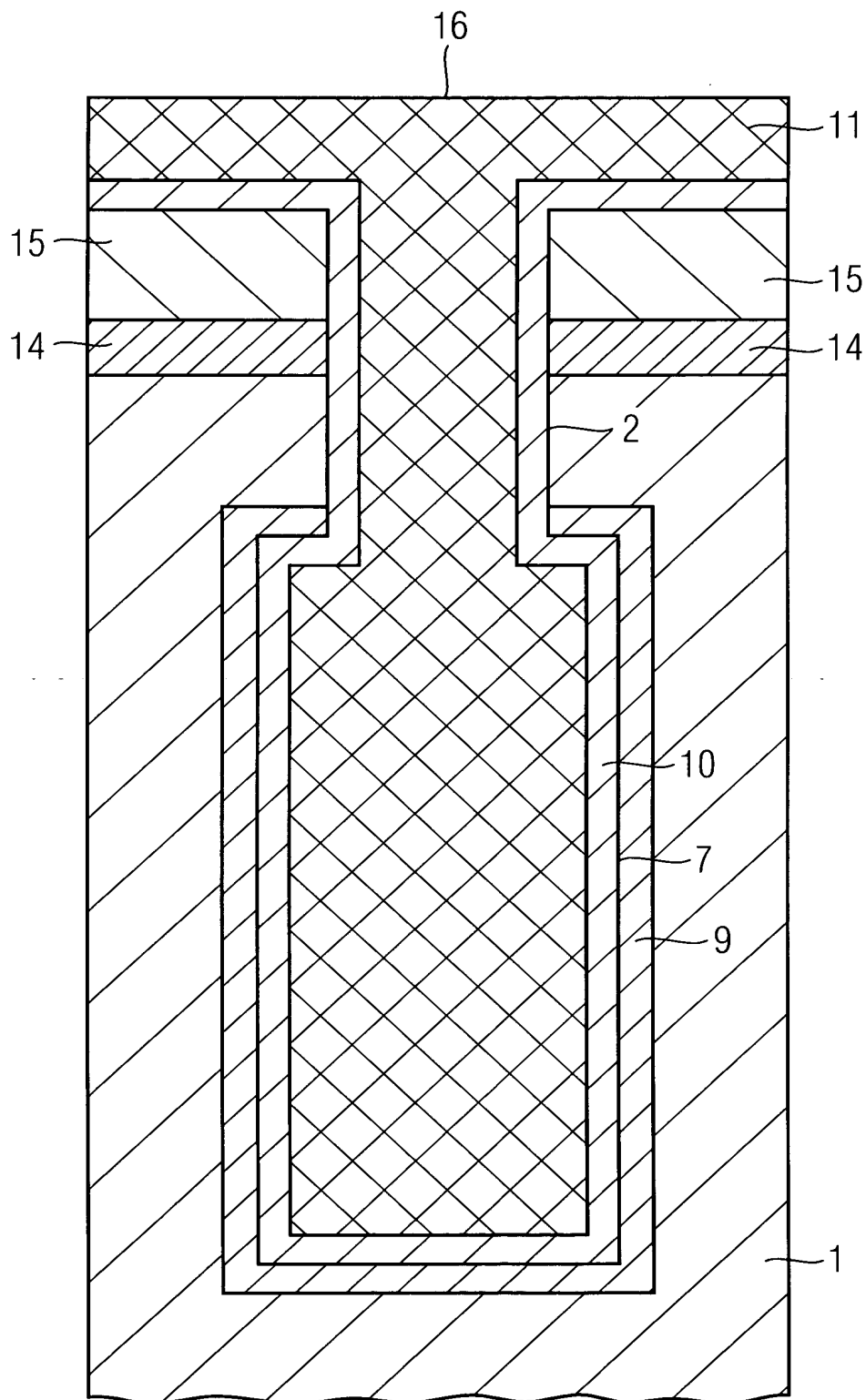


FIG 2A

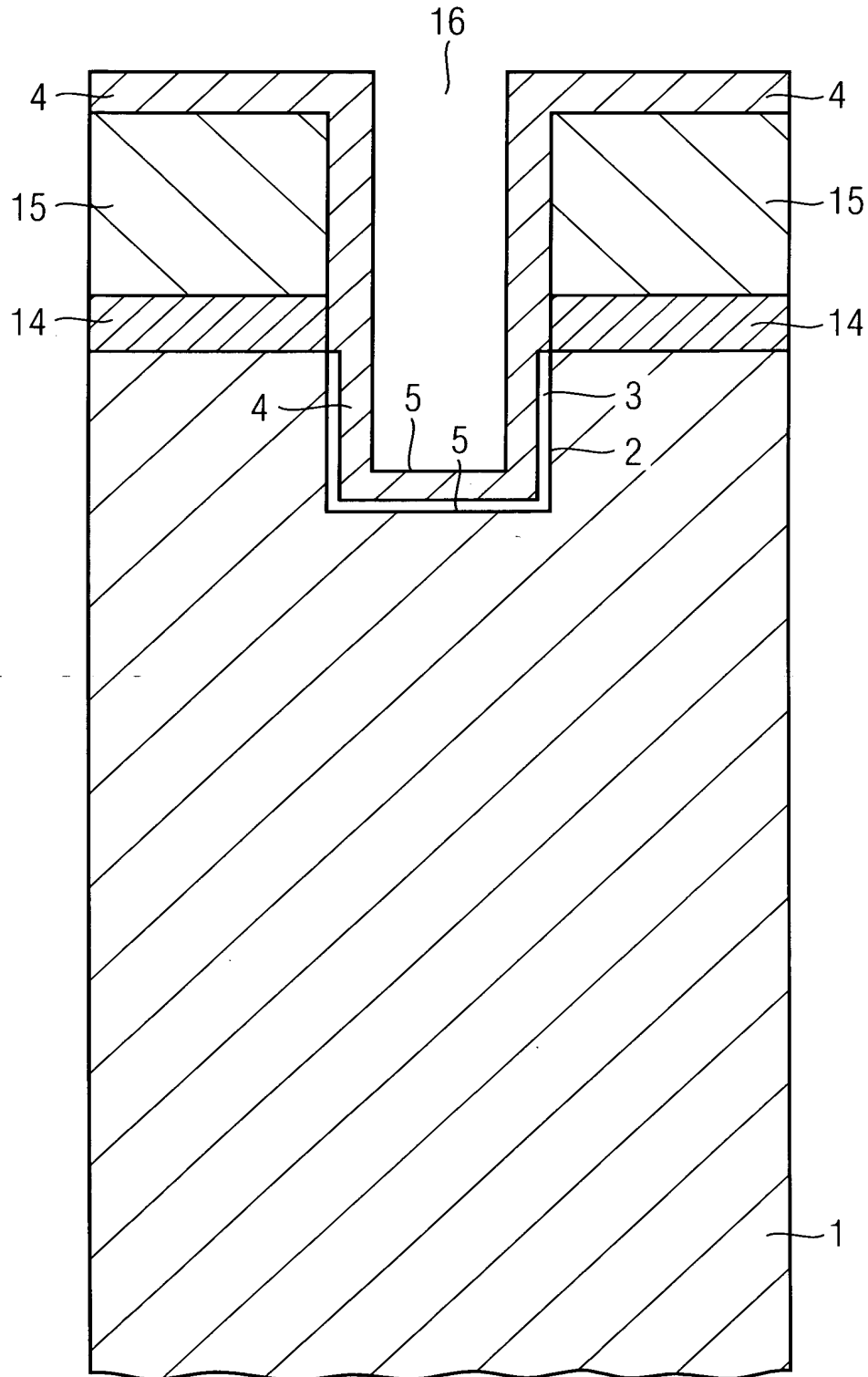


FIG 2B

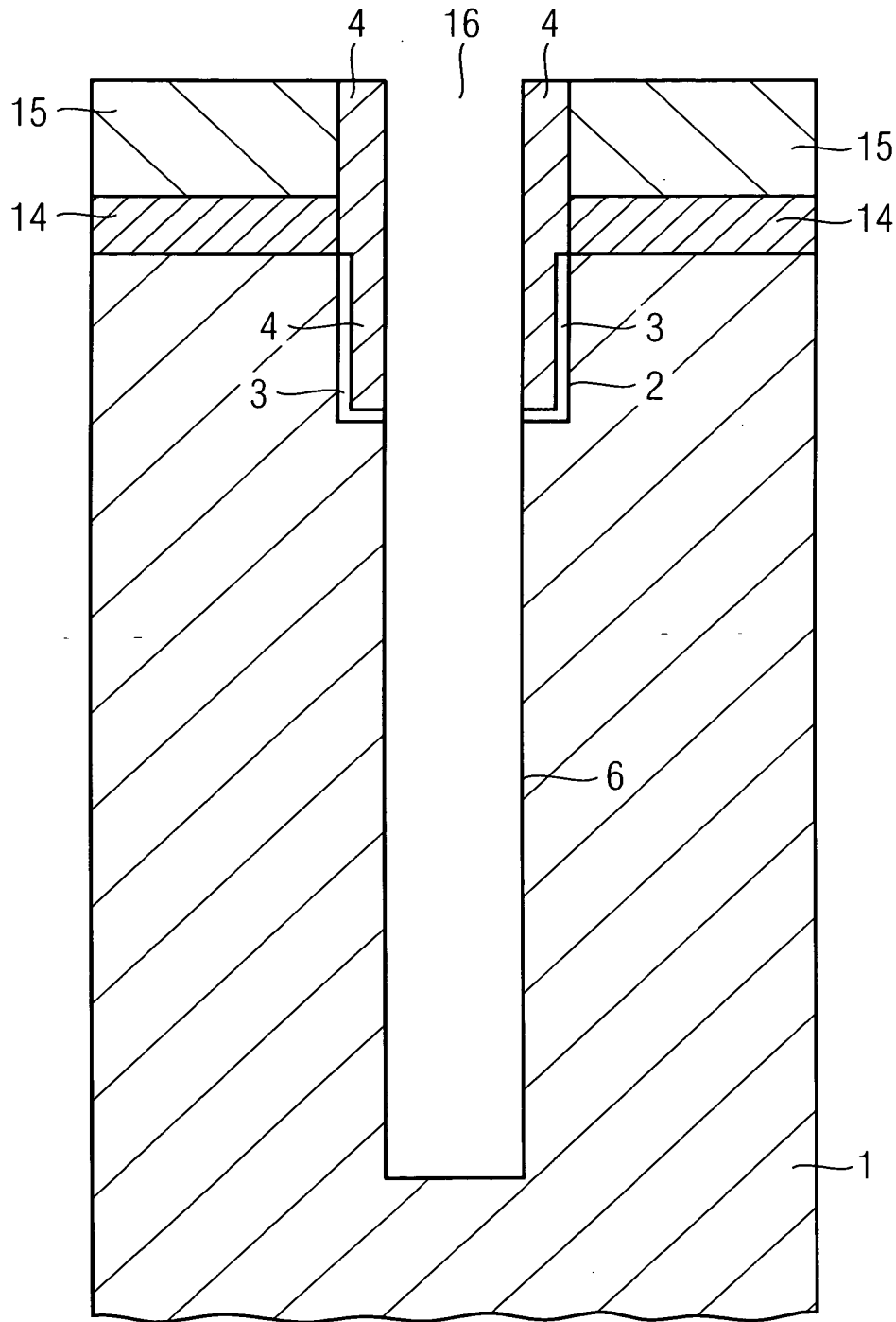


FIG 2C

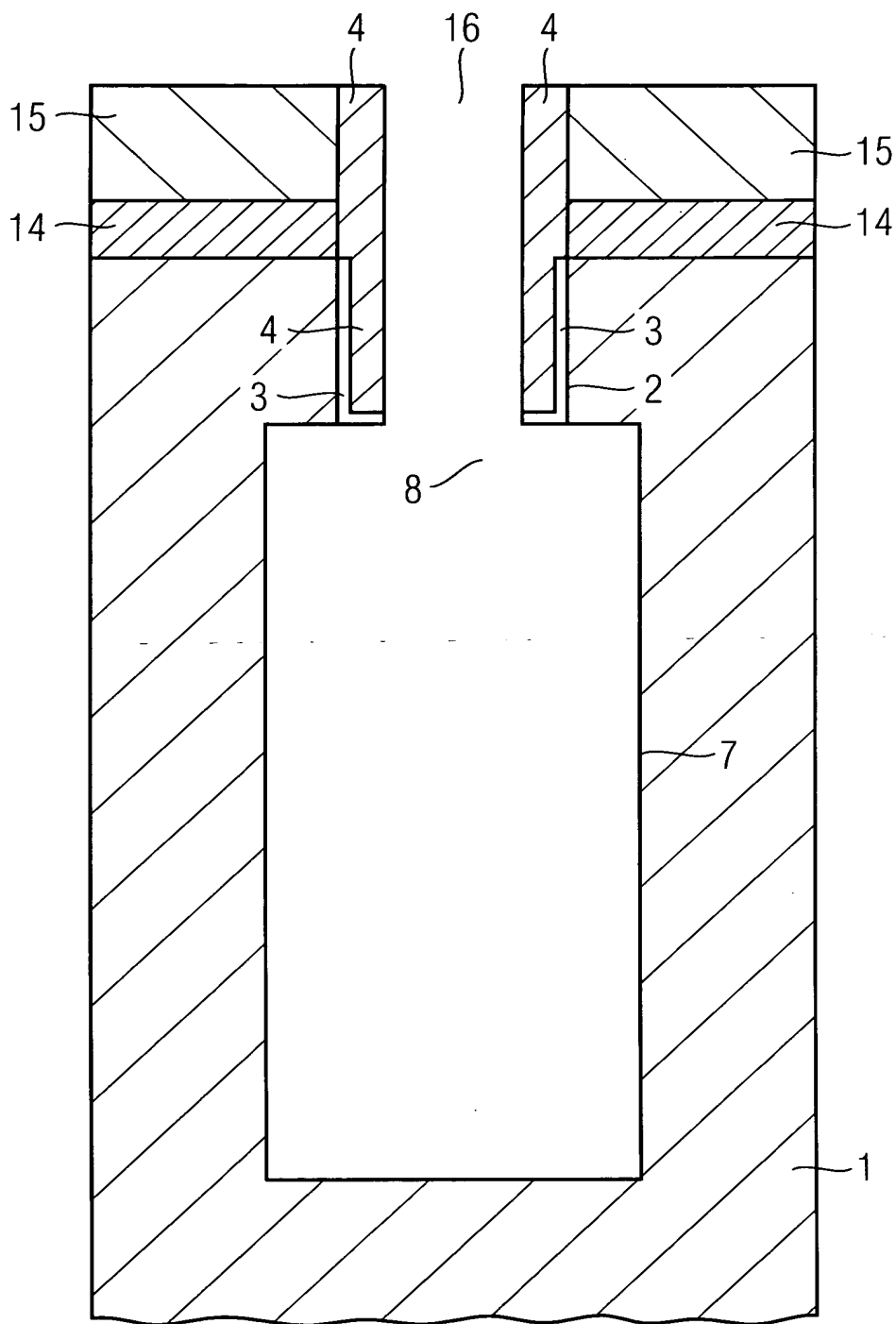


FIG 2D

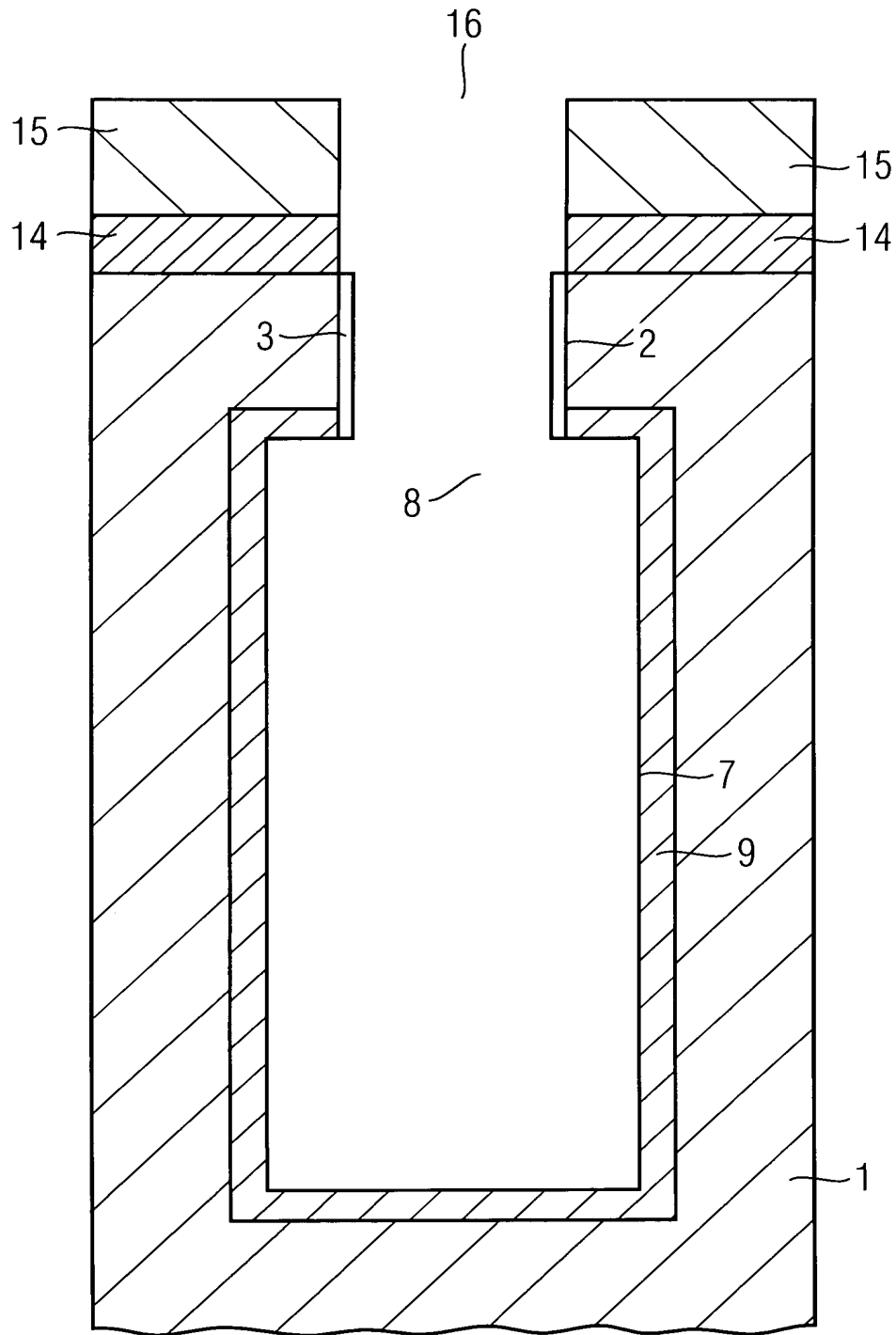


FIG 2E

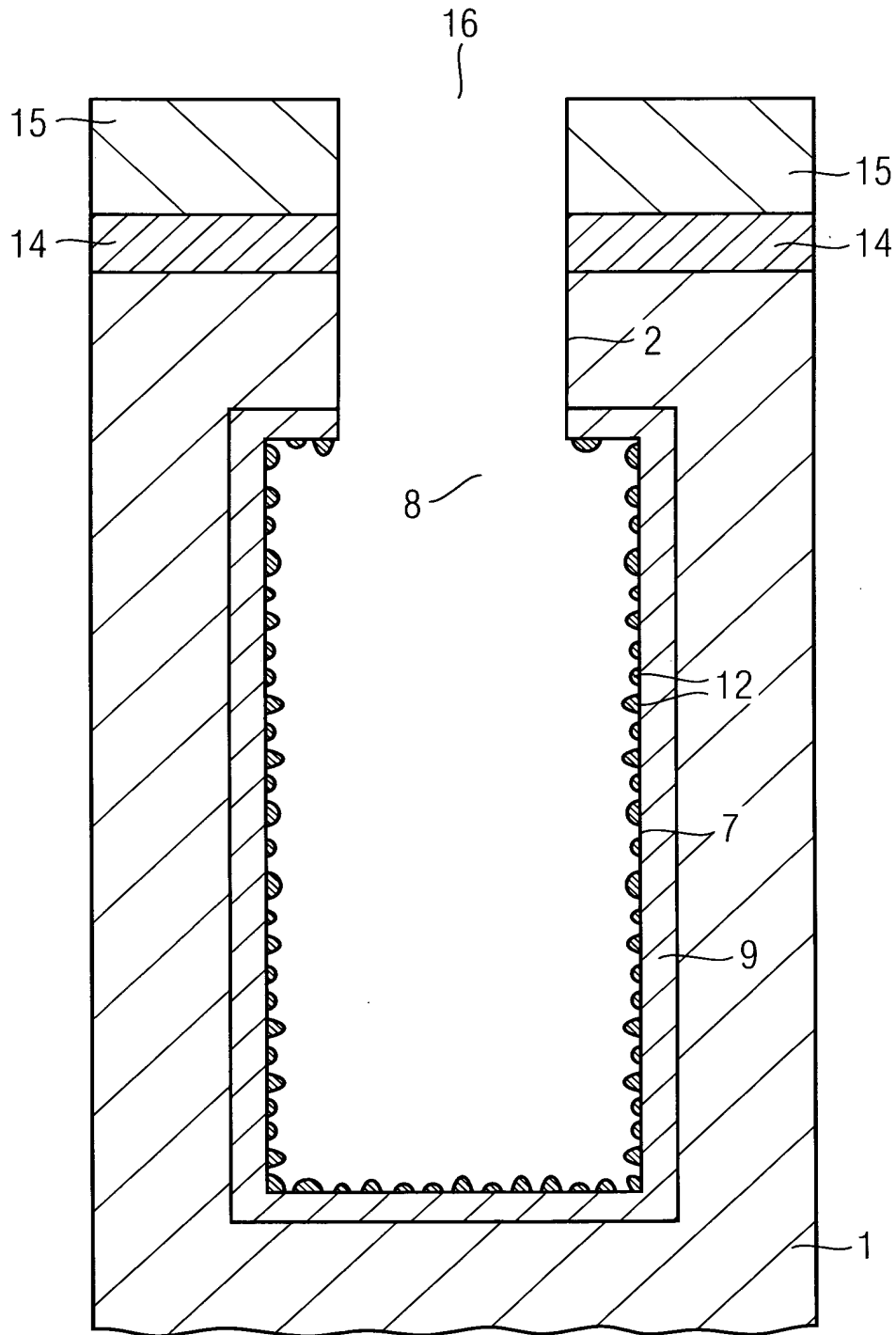


FIG 2F

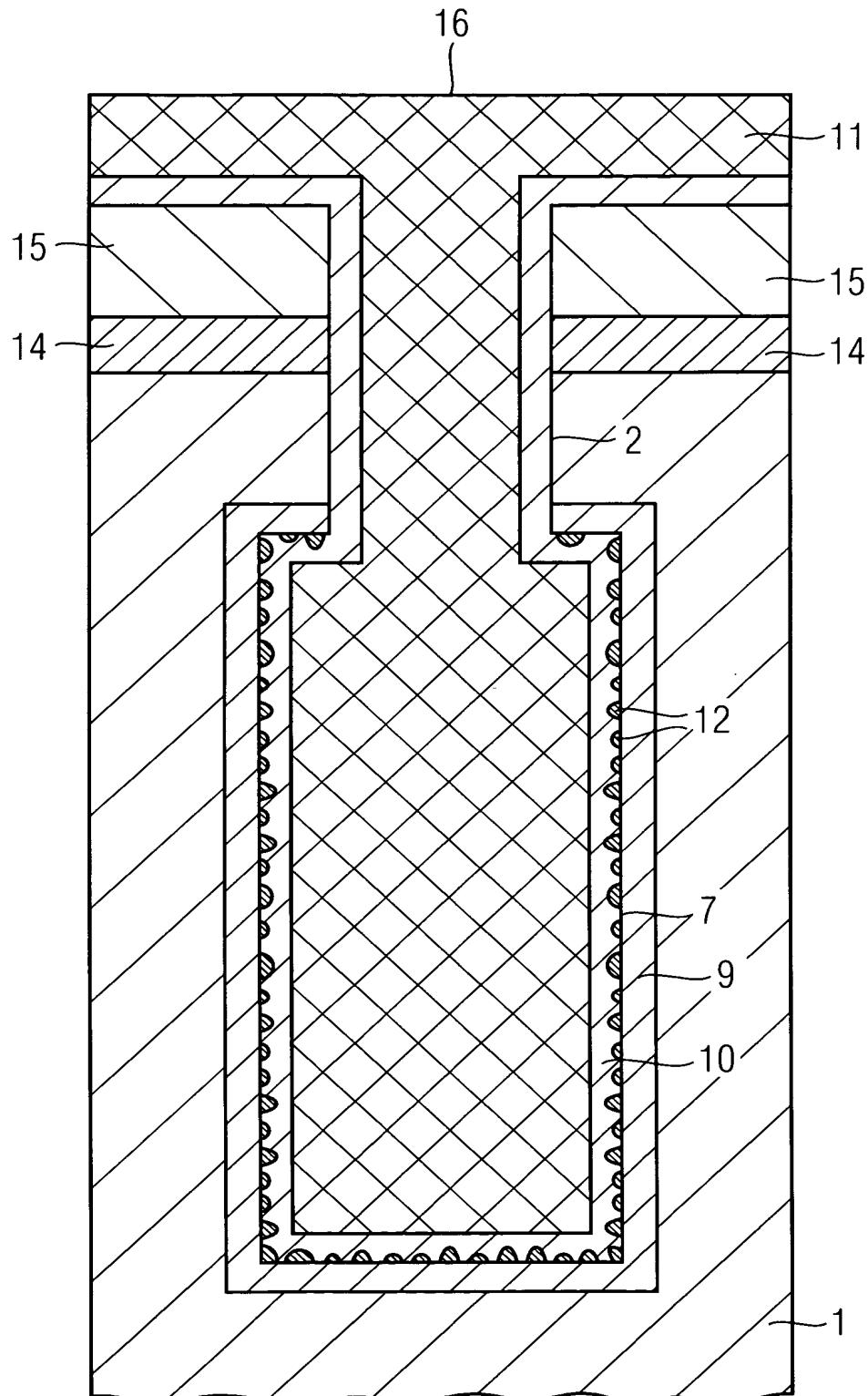


FIG 2G

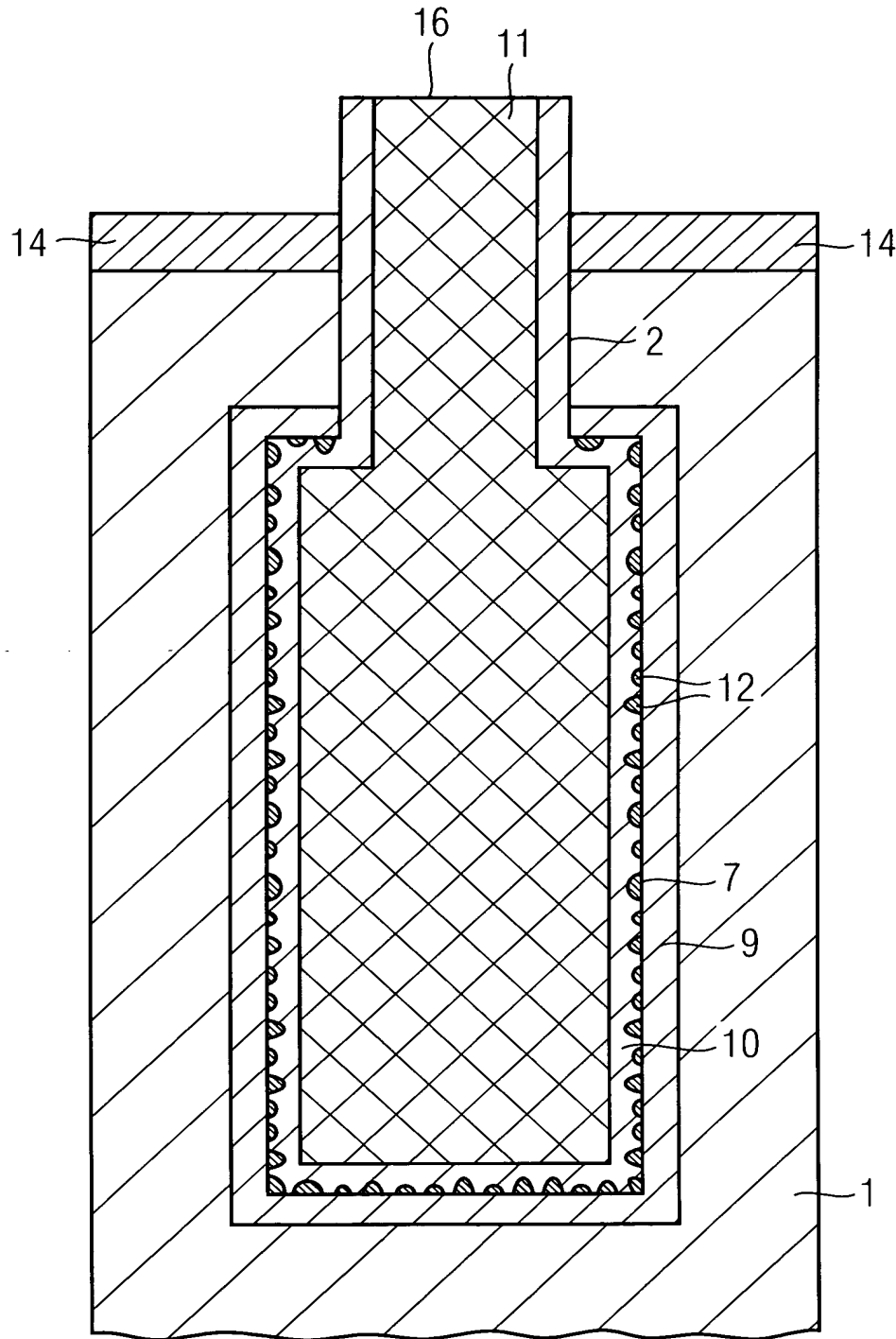


FIG 2H

